Supporting information:

Molecular level controlled fabrication of highly transparent conductive reduced graphene oxide/Ag nanowire hybrid film

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Fig. S1 Image of the Langmuir-Blodgett (L-B) trough, showing the transfer process of the UL-GO sheets onto the quartzes substrate.



Fig. S2 XRD spectrum of expanded graphite and 514 nm Raman spectrum of the graphene oxide. The peak around 13.5° indicates an interlayer spacing of 0.61 nm. And the peak around 27° indicate that the interlayer of the expanded graphite were not separated completely as graphene oxide¹. *D* peak and *D*+*G* peak, which refer to the defect of the graphene oxide are around ~1350 cm⁻¹ and ~2900 cm⁻¹. *G* peak and 2*D*+*G* peak referring to the crystallinity of the graphene oxide are around ~1580 cm⁻¹ and ~2700 cm⁻¹. The intensity ratio of I_D/I_G and I_{D+G}/I_{2D} often used for estimating the *sp*² domain size of graphite-based materials. As the ratio of I_D/I_G and I_{D+G}/I_{2D} are 0.82 and 1.39. It showed the graphene oxide was well oxygenated as the

ratio of is I_{D+G}/I_{2D} more sensitive².

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Table S1 Relative percentages of carbon and assignations of UL-GO and rUL-GO.

Binding energy and	$Cg(sp^2)$	Cd(<i>sp</i> ³)	C-0	С=О	-0-C=0
assignation	~284.9eV	~285.6eV	~287.1eV	~288.1eV	~290.0eV
UL-GO	36.5%	21.5%	21.8%	13.6%	6.6%
rUL-GO	74.7%	13%	4.2%	4%	4.1%

Table S2 DC to optical conductivity ratio of current work and other works.

Method	Materials	SR (Ω /sq)	T (%)	σ_{DC}/σ_{Op}	Reference
L-B Spin-coating	GO / Ag NW	13	71.9	81	Current Work
	Graphene / Ag NW	64	94	93.7	Kholmanov et al. ³
CVD Doping	Graphene Ag NW/	202	96	45.3	Shin et al. ⁴
Spin-coating	GO CNT/	86	80	18.6	Gao et al. ⁵
	GO/ Ag NW- Au NP	26	83	74.2	Kholmanov et al. ⁶
Self-assembly	GO/ Ag NW	86	80	19.8	Tien et al. ⁷
Dip coating	GO/ Ag NW	150	86	16.0	Yun et al. ⁸
Transfer printing	GO/ Ag NW	27	80	59.1	Zhang et al.9
	GO/ Ag NW	210	97	58.5	Domingues et al. ¹⁰
Vacuum filtration	GO/ Ag NP	93	78	15.3	Tien et al. ¹¹

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